

FDMS8670S

N-Channel PowerTrench® SyncFET™

30V, 42A, 3.5mΩ

Features

- Max $r_{DS(on)}$ = 3.5mΩ at $V_{GS} = 10V$, $I_D = 20A$
- Max $r_{DS(on)}$ = 5.0mΩ at $V_{GS} = 4.5V$, $I_D = 17A$
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- SyncFET Schottky Body Diode
- MSL1 robust package design
- RoHS Compliant

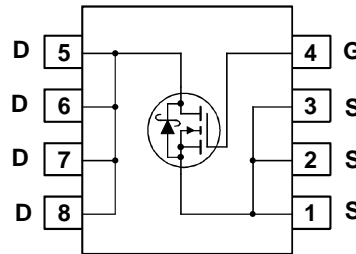
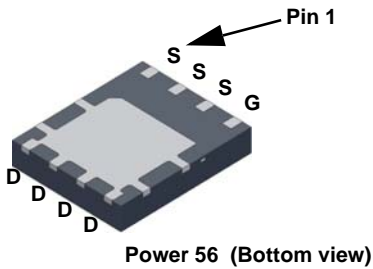


General Description

The FDMS8670S has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.

Application

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU low side switch
- Networking Point of Load low side switch
- Telecom secondary side rectification



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|--|-------------|------------------|
| V_{DS} | Drain to Source Voltage | 30 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$ | 42 | A |
| | -Continuous (Silicon limited) $T_C = 25^\circ\text{C}$ | 116 | |
| | -Continuous (Silicon limited) $T_C = 100^\circ\text{C}$ | 74 | |
| | -Continuous $T_A = 25^\circ\text{C}$ | 20 | |
| | -Pulsed | 200 | |
| P_D | Power Dissipation $T_C = 25^\circ\text{C}$ | 78 | W |
| | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) | 2.5 | |
| | Power Dissipation $T_A = 85^\circ\text{C}$ (Note 1a) | 1.3 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 1.6 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 50 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------|----------|-----------|------------|------------|
| FDMS8670S | FDMS8670S | Power 56 | 13" | 12mm | 3000 units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|--|----|----|-----------|----------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 1\text{mA}, V_{GS} = 0\text{V}$ | 30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 10\text{mA}$, referenced to 25°C | | 17 | | $\text{mV}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$ | | | 500 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ | | | ± 100 | nA |

On Characteristics

| | | | | | | |
|--|--|--|---|------|-----|----------------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 1\text{mA}$ | 1 | 1.5 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 50\text{mA}$, referenced to 25°C | | -2.8 | | $\text{mV}/^\circ\text{C}$ |
| $r_{DS(on)}$ | Drain to Source On Resistance | $V_{GS} = 10\text{V}, I_D = 20\text{A}$ | | 2.8 | 3.5 | m Ω |
| | | $V_{GS} = 4.5\text{V}, I_D = 17\text{A}$ | | 3.6 | 5.0 | |
| | | $V_{GS} = 10\text{V}, I_D = 20\text{A}, T_J = 125^\circ\text{C}$ | | 3.9 | 6.0 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 10\text{V}, I_D = 20\text{A}$ | | 98 | | S |

Dynamic Characteristics

| | | | | | | |
|------------|------------------------------|--|--|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 15\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$ | | 3005 | 4000 | pF |
| C_{oss} | Output Capacitance | | | 865 | 1150 | pF |
| C_{riss} | Reverse Transfer Capacitance | | | 320 | 480 | pF |
| R_g | Gate Resistance | $f = 1\text{MHz}$ | | 1.4 | 5.0 | Ω |

Switching Characteristics

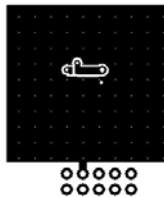
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|---------------|-------------------------------|---|---|----|----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 15\text{V}, I_D = 20\text{A}$ $V_{GS} = 10\text{V}, R_{GEN} = 5\Omega$ | | 14 | 26 | ns | |
| t_r | Rise Time | | | 19 | 35 | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 37 | 60 | ns | |
| t_f | Fall Time | | | 10 | 20 | ns | |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | | $V_{GS} = 0\text{V}$ to 10V | | 52 | 73 | nC |
| $Q_{g(4.5V)}$ | Total Gate Charge at 4.5V | $V_{GS} = 0\text{V}$ to 4.5V | $V_{DS} = 15\text{V}$ $I_D = 20\text{A}$ | | 24 | 34 | nC |
| Q_{gs} | Gate to Source Gate Charge | | | | 8 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | | 10 | | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|---------------------------------------|---|--|-----|-----|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = 2\text{A}$ | | 0.4 | 0.7 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 20\text{A}, di/dt = 300\text{A}/\mu\text{s}$ | | 26 | 42 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 24 | 39 | nC |

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5×1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse time $< 300\mu\text{s}$, Duty cycle $< 2\%$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

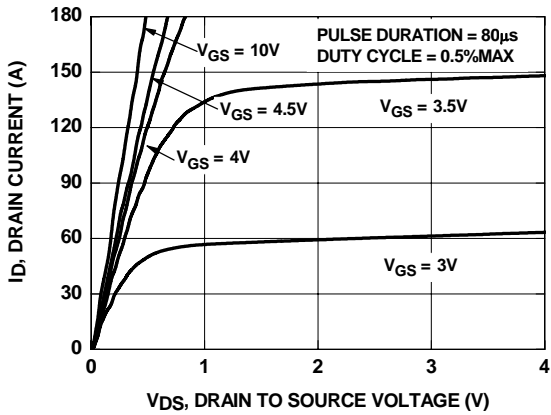


Figure 1. On Region Characteristics

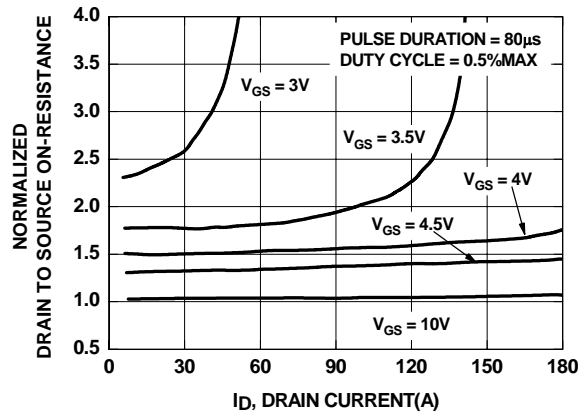


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

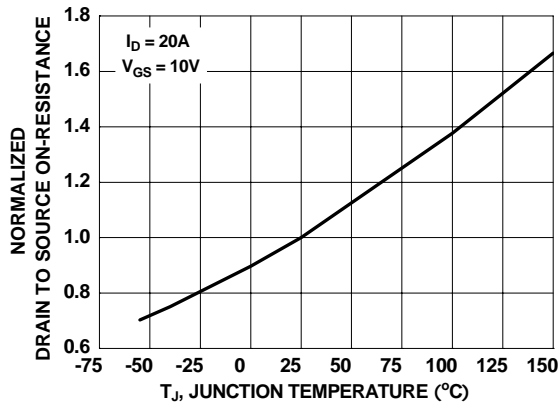


Figure 3. Normalized On Resistance vs Junction Temperature

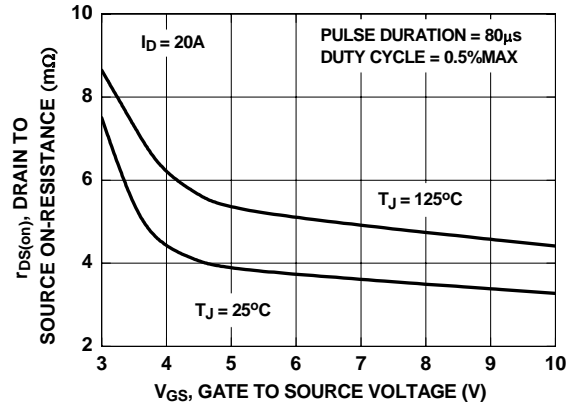


Figure 4. On-Resistance vs Gate to Source Voltage

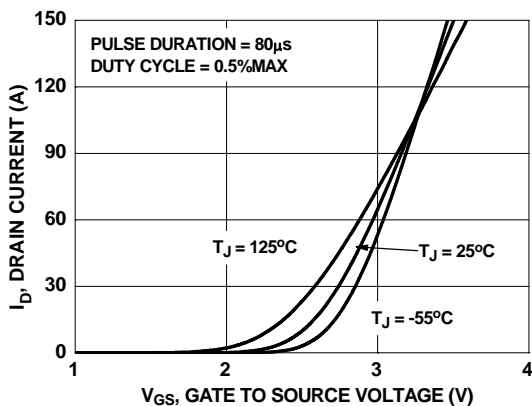


Figure 5. Transfer Characteristics

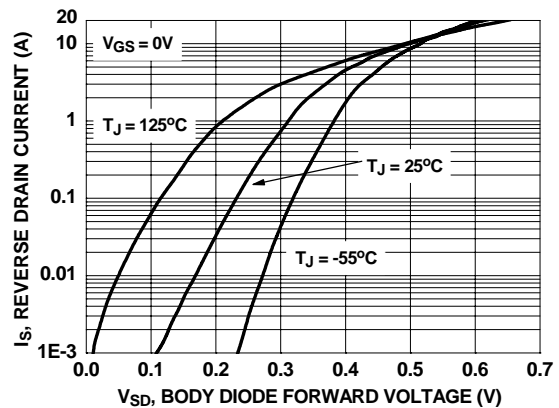


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

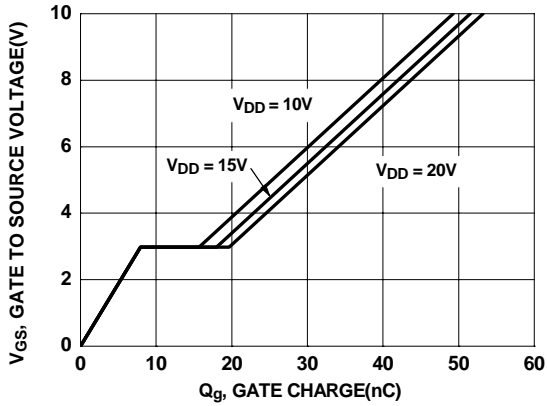


Figure 7. Gate Charge Characteristics

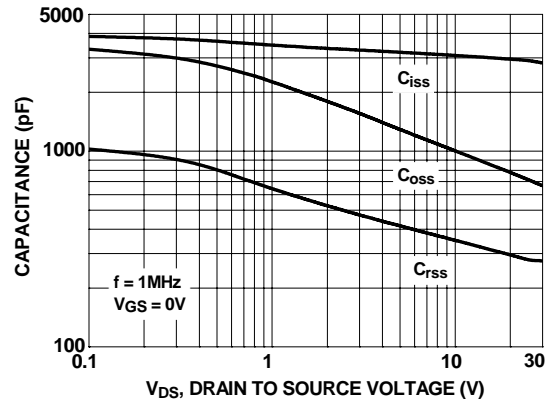


Figure 8. Capacitance vs Drain to Source Voltage

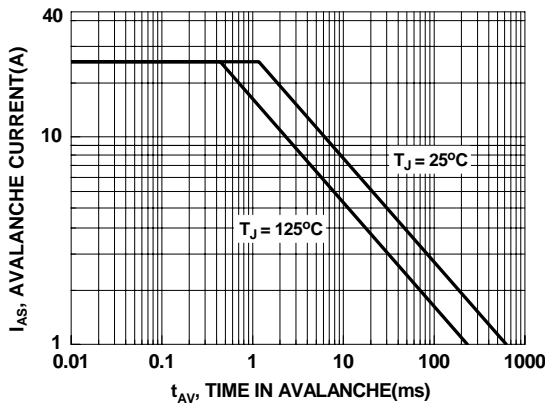


Figure 9. Unclamped Inductive Switching Capability

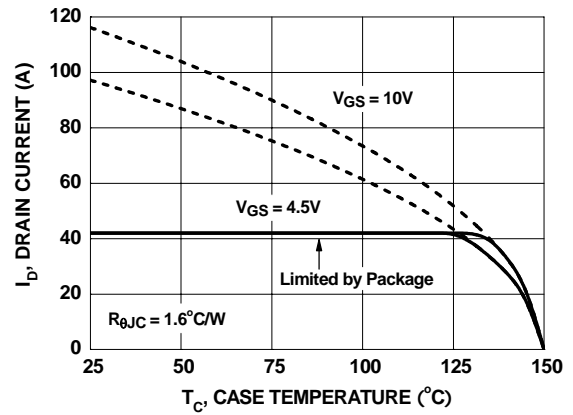


Figure 10. Maximum Continuous Drain Current vs Case Temperature

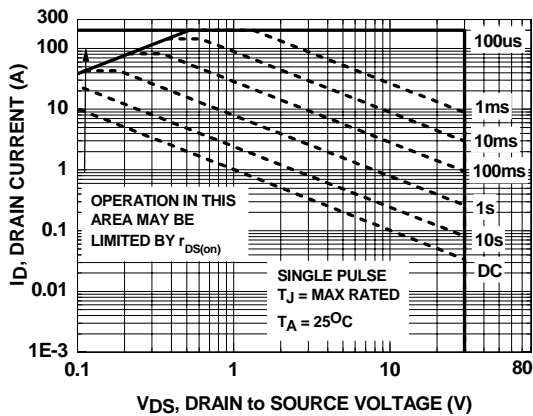


Figure 11. Forward Bias Safe Operating Area

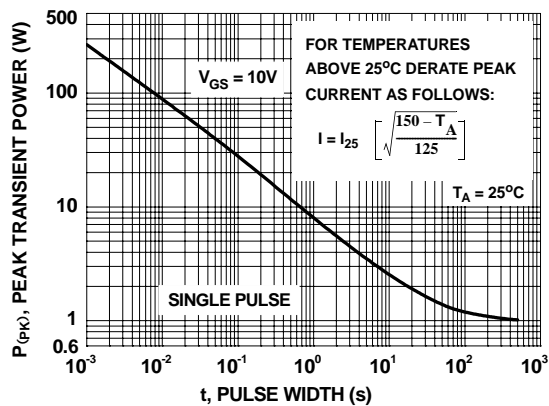


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

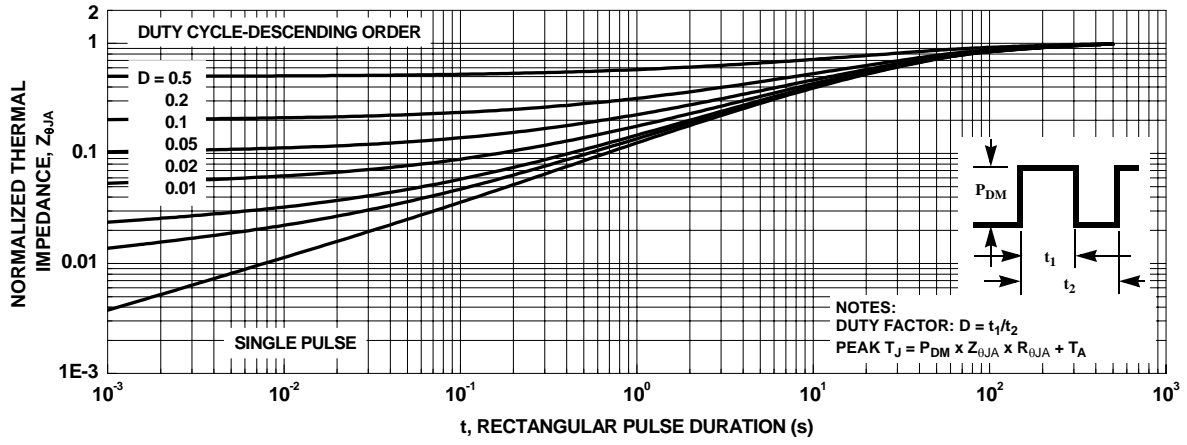


Figure 13. Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky body diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS8670S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

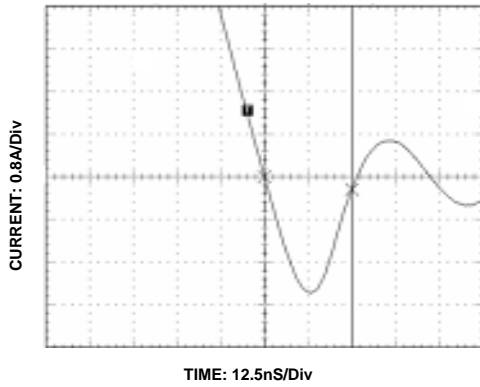


Figure 14. FDMS8670S SyncFET Body Diode reverse recovery characteristics

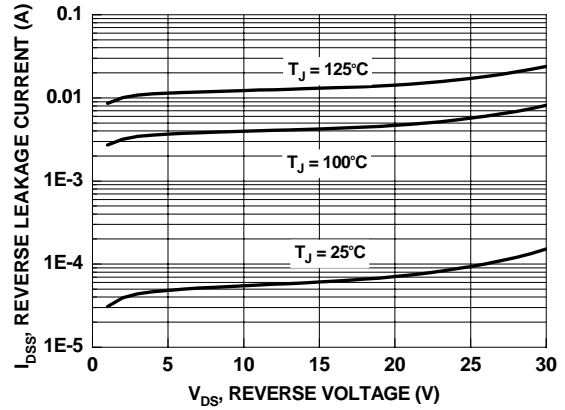
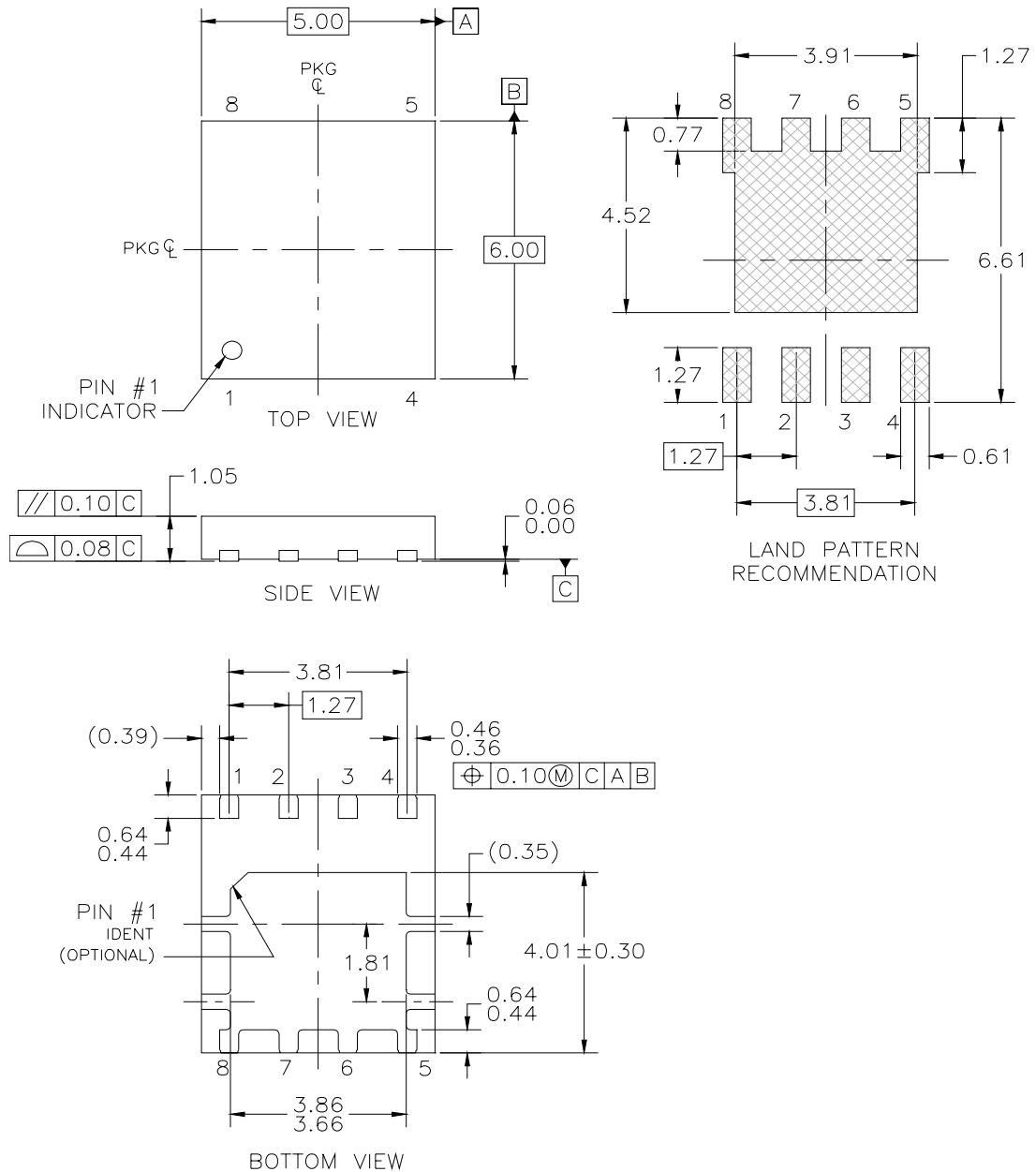


Figure 15. SyncFET Body Diode reverse leakage vs drain to source voltage






- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) NO JEDEC REFERENCE AS OF FEBRUARY 2006
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994

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